



## 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-75 A

### **Features**

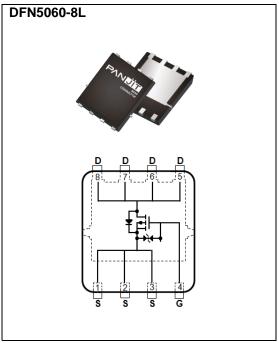
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V, I<sub>D</sub>@-20A<8.4mΩ
- RDS(ON), VGS@-4.5V, ID@-10A<13.5m $\Omega$
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case : DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.08 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETE	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Voltage		V <sub>GS</sub>	±25	V	
Continuous Drain Current(Note 3)	T <sub>C</sub> =25°C		-75		
	T <sub>C</sub> =100°C	I <sub>D</sub>	-53	А	
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-215		
Power Dissipation	T <sub>C</sub> =25°C	<b>D</b>	75	10/	
	T <sub>C</sub> =100°C	Pb —	38	W	
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C		-15.7	Δ.	
	T <sub>A</sub> =70°C	I <sub>D</sub>	-13.2	A	
Power Dissipation	T <sub>A</sub> =25°C	D-	3.3	10/	
	T <sub>A</sub> =70°C	PD	2.3	W	
Single Pulse Avalanche Energy(Note 5)		Eas	121	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Thormal Decistor as (Note 4)	Junction to Case	R <sub>0JC</sub>	2	°C/W	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Ambient	R <sub>θJA</sub>	45	C/VV	





### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA -1		-1.7	-2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	6.7	8.4	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	10.4	13.5		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA	
Gate-Source Leakage Current		V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V	-	-	±10		
	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±1	uA	
Dynamic <sup>(Note 6)</sup>	_						
Total Gate Charge	Qg	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	54	-	nC	
Gate-Source Charge	Qgs	V <sub>DS</sub> =-24V, I <sub>D</sub> =-20A,	-	6	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =-10V	-	17	-		
Input Capacitance	Ciss	)/ 05\/ \/ 0\/	-	2310	-		
Output Capacitance	Coss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHz	-	332	-	pF	
Reverse Transfer Capacitance	Crss	I=IIVIDZ	-	256	-		
Gate resistance	Rg	f=1MHz	-	2.3	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	\/ O4\/   O04	-	11	-	ns	
Turn-On Rise Time	tr	V <sub>DS</sub> =-24V, I <sub>D</sub> =-20A,	-	9	-		
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=-10V$ , $R_{G}=3\Omega$	-	37	-		
Turn-Off Fall Time	tf	(11010 2)	-	21	-		
Drain-Source Diode							
Diode Forward Current	Is	Tc=25°C	-	-	-75	A	
Pulsed Diode Forward Current	I <sub>SM</sub>	TC=25 C	-	-	-215		
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-20A, V <sub>GS</sub> =0V	-	-0.85	-1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A	-	22	-	ns	
Reverse Recovery Charge	Qrr	dl <sub>S</sub> /dt=100A/us	-	10	-	nC	

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH,  $I_{AS}$ =-22A,  $V_{DD}$ =-30V,  $V_{GS}$ =-10V, Starting  $T_{J}$ =25°C.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

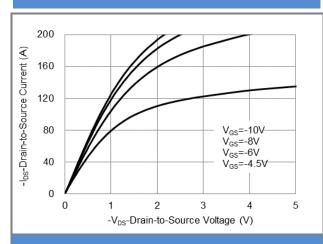
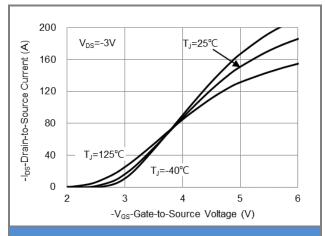


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

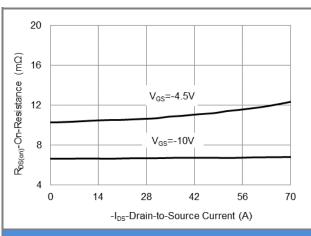


Fig.3 On-Resistance vs. Drain Current

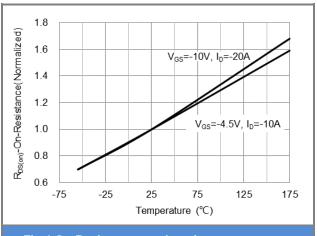


Fig.4 On-Resistance vs. Junction temperature

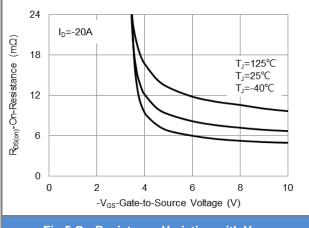


Fig.5 On-Resistance Variation with V<sub>GS</sub>

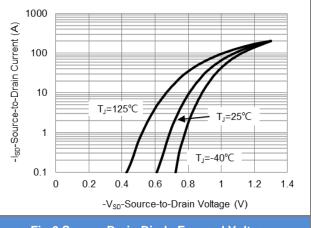


Fig.6 Source-Drain Diode Forward Voltage





#### **TYPICAL CHARACTERISTIC CURVES**

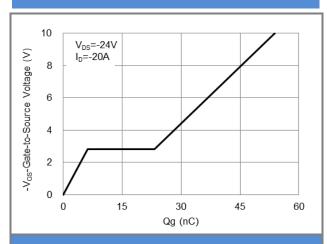


Fig.7 Gate-Charge Characteristics

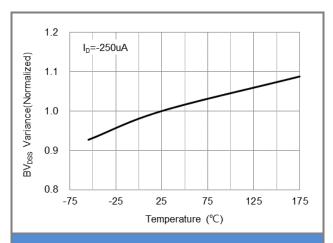


Fig.8 Breakdown Voltage Variation vs. Temperature

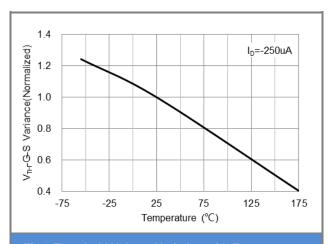


Fig.9 Threshold Voltage Variation with Temperature

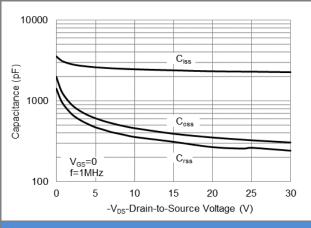
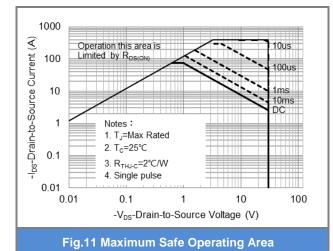
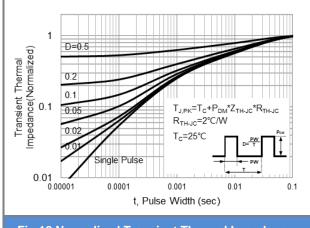


Fig.10 Capacitance vs. Drain-Source Voltage





**Fig.12 Normalized Transient Thermal Impedance** 

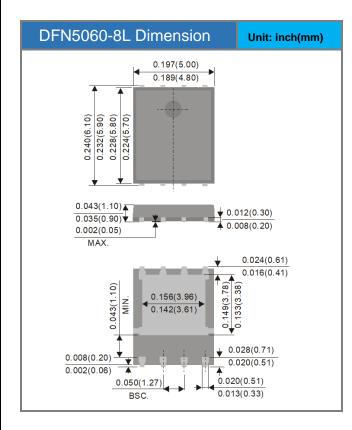


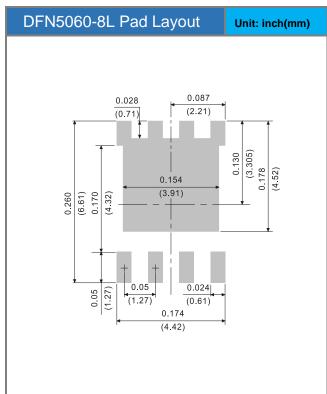


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ5433E-AU	DFN5060-8L	3K pcs / 13" reel	Q5433E	

## **Packaging Information & Mounting Pad Layout**









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